

# Silicon Rf Power Mos Fet Discrete Rd70huf2

## [DOC] Silicon Rf Power Mos Fet Discrete Rd70huf2

Eventually, you will certainly discover a extra experience and attainment by spending more cash. nevertheless when? complete you understand that you require to acquire those all needs next having significantly cash? Why dont you try to get something basic in the beginning? Thats something that will guide you to comprehend even more with reference to the globe, experience, some places, subsequently history, amusement, and a lot more?

It is your categorically own get older to accomplish reviewing habit. along with guides you could enjoy now is [Silicon Rf Power Mos Fet Discrete Rd70huf2](#) below.

### Silicon Rf Power Mos Fet

#### < Silicon RF Power MOS FET (Discrete) > RD30HVF1

< Silicon RF Power MOS FET (Discrete) > RD30HVF1 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 30W DESCRIPTION RD30HVF1 is a MOS FET type transistor specifically designed for VHF RF power amplifiers applications FEATURES High power gain: Pout>30W, Gp>147dB @Vdd=125V, f=175MHz High Efficiency: 60%typ APPLICATION

#### **SILICON RF POWER MOSFETS - World Scientific**

x SILICON RF POWER MOSFETS the packaging and RF testing team from Silicon Semiconductor Corporation for their roles in developing SL-MOSFET products for cellular base-station applications This book was prepared, after my return to academi 2003a i a,ns a part of my scholarly activities at North Carolina State University Once

#### < Silicon RF Power MOS FET (Discrete) > RD70HVF1

< Silicon RF Power MOS FET (Discrete) > RD70HVF1 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz 70W 520MHz, 50W DESCRIPTION RD70HVF1 is a MOS FET type transistor specifically designed for VHF/UHF High power amplifiers applications FEATURES High power and High Gain: Pout>70W, Gp>106dB @Vdd=125V, f=175MHz Pout>50W, Gp>70dB ...

#### < Silicon RF Power MOS FET (Discrete) > RD15HVF1

< Silicon RF Power MOS FET (Discrete) > RD15HVF1 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz 520MHz, 15W DESCRIPTION RD15HVF1 is a MOS FET type transistor specifically designed for VHF/UHF High power amplifiers applica-tions FEATURES High power and High Gain: Pout>15W, Gp>14dB @Vdd=125V, f=175MHz Pout>15W, ...

#### < Silicon RF Power MOS FET (Discrete) > RD70HUF2

< Silicon RF Power MOS FET (Discrete) > RD70HUF2 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 530MHz, 70W DESCRIPTION

RD70HUF2 is MOS FET type transistor specifically designed for VHF/UHF RF power amplifiers applications FEATURES 1 Supply with Tape and Reel 500 Units per Reel 2 Employing Mold Package 3 High Power ...

**< Silicon RF Power MOS FET (Discrete) > RD100HHF1**

< Silicon RF Power MOS FET (Discrete) > RD100HHF1 RoHS Compliance, Silicon MOSFET Power Transistor 30MHz,100W DESCRIPTION

RD100HHF1 is a MOS FET type transistor specifically designed for HF High power amplifiers applications FEATURES High power and High Gain: Pout>100W, Gp>115dB @Vdd=125V,f=30MHz High Efficiency: 60%typon HF Band ...

**< Silicon RF Power MOS FET (Discrete) > RD06HVF1**

< Silicon RF Power MOS FET (Discrete) > RD06HVF1 RoHS Compliance, Silicon MOSFET Power Transistor 175MHz,6W DESCRIPTION RD06HVF1

is a MOS FET type transistor specifically designed for VHF RF power amplifiers applications FEATURES High power gain: Pout>6W, Gp>13dB @Vdd=125V,f=175MHz APPLICATION For output stage of high power ...

**< Silicon RF Power MOS FET (Discrete) > RD15HVF1**

< Silicon RF Power MOS FET (Discrete) > RD15HVF1 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 15W DESCRIPTION

RD15HVF1 is a MOS FET type transistor specifically designed for VHF/UHF High power amplifiers applications FEATURES High power and High Gain: Pout>15 W, Gp>14 dB @Vds=125 V,f=175 MHz High Efficiency: 60 1% (typ) ...

**SILICON RF POWER MOSFETS - GBV**

XVI SILICON RF POWER MOSFETs Chapter9 Dual Trench MOSFETs 219 91 Device Cell Structure 220 92 DT-MOSFET Simulation Structure 223 93 DT-MOSFET Blocking Characteristics 225 94 DT-MOSFET On-State Characteristics "" 228 95 DT-MOSFET Output and Transfer Characteristics 229 96 DT-MOSFET Capacitances 231 97 DT-MOSFET RF ...

**< Silicon RF Power MOS FET (Discrete) > RD01MUS2B**

< Silicon RF Power MOS FET (Discrete) > RD01MUS2B RoHS Compliance, Silicon MOSFET Power Transistor 527MHz,1W DESCRIPTION

RD01MUS2B is a MOS FET type transistor specifically designed for VHF/UHF RF amplifiers applications This device has an internal monolithic zener diode from gate to source for ESD protection FEATURES

**< Silicon RF Power MOS FET (Discrete) > RD12MVS1**

< Silicon RF Power MOS FET (Discrete) > RD12MVS1 RoHS Compliant, Silicon MOSFET Power Transistor, 175MHz, 12W PublicationDate:Sep[]2014

2 ELECTRICAL CHARACTERISTICS (Tc=25°C, UNLESS OTHERWISE NOTED) SYMBOL PARAMETER CONDITIONS

**< Silicon RF Power MOS FET (Discrete) > RD60HUF1**

< Silicon RF Power MOS FET (Discrete) > RD60HUF1 RoHS Compliance, Silicon MOSFET Power Transistor 520MHz,60W DESCRIPTION

RD60HUF1 is a MOS FET type transistor specifically designed for UHF High power amplifiers applications FEATURES High power and High Gain: Pout>60W, Gp>77dB @Vdd=125V,f=520MHz High Efficiency: 55%typon UHF ...

**Silicon RF Power MOS FET (Discrete) > RD70HVF1C**

Silicon RF Power MOS FET (Discrete) > RD70HVF1C RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz 70W , 520MHz 50W

DESCRIPTION RD70HVF1C is a MOS FET type transistor specifically designed for VHF/UHF High power amplifiers applications FEATURES High power and High Gain: Pout>70W, Gp>106dB @Vds=125V,f=175MHz

**Power Semiconductors Power Modules RF Power MOSFETs**

• Defense and oil drilling: Motor drives, auxiliary power supplies SiC MOSFET and SiC Schottky barrier diode product lines from Microsemi increase your system efficiency over silicon MOSFET and IGBT solutions while lowering your total cost of ownership by enabling downsized systems and smaller/lower cost cooling TO-268 D3PAK TO-247

#### **SILICON RF POWER MOSFET - Advanced Semiconductor**

ψ VSWR = 30:1 AT ALL PHASE ANGLES NO DEGRADATION IN OUTPUT POWER SILICON RF POWER MOSFET MRF150 DESCRIPTION: The MRF150 is an N-Channel Enhancement-Mode MOS Broadband RF Power Transistor Designed for Wideband Large Signal Amplifier Applications From 20 to 150 MHz MAXIMUM RATINGS ID 16 A VDSS 125 V VGS ...

#### **< Silicon RF Power MOS FET (Discrete) > RD07MVS1**

< Silicon RF Power MOS FET (Discrete) > RD07MVS1 RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz, 520MHz, 7W, 72V Publication Date : May 2017 3 TYPICAL CHARACTERISTICS (These are only typical curves and devices are not necessarily guaranteed at these curves) S 0 10 20 30 40 50 60 0 40 80 120 160 200 CHANNEL DISSIPATION

#### **SILICON RF DEVICES - RFMW Ltd.**

Silicon RF Devices FET Hybrid IC MAP For SELECTION PRODUCT LIST HIGH OUTPUT POWER Si MOS FET (DISCRETE) □: New Product □□: Under Development Frequency [MHz] Better Performance for Radio Communication Network Mitsubishi Electric Silicon RF Devices are Key parts of RF Power Amplifications for various kind of Mobile Radio, Professional Mobile ...